

RB160M-40 Silicon Epitaxial Planar Schottky Barrier Diode

Features

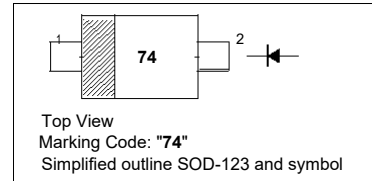
- High reliability
- Low forward voltage

Application

- For switching power supplies
- Battery protection against reversal current

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



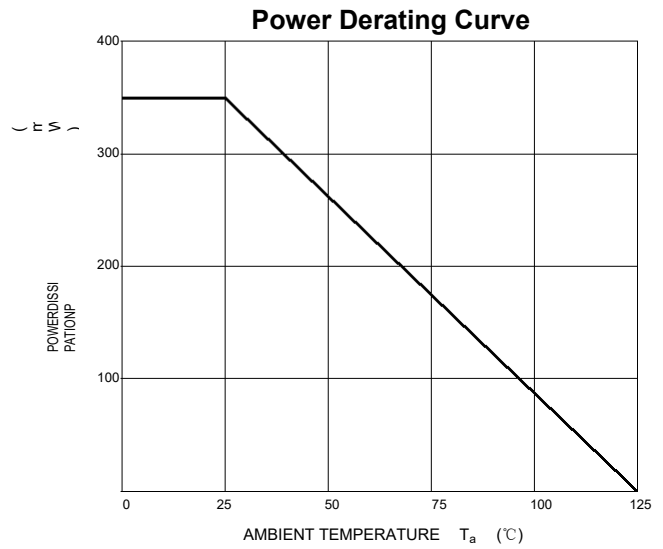
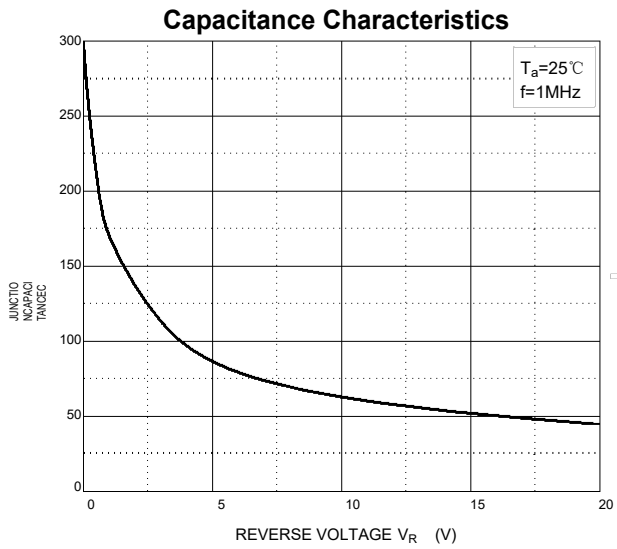
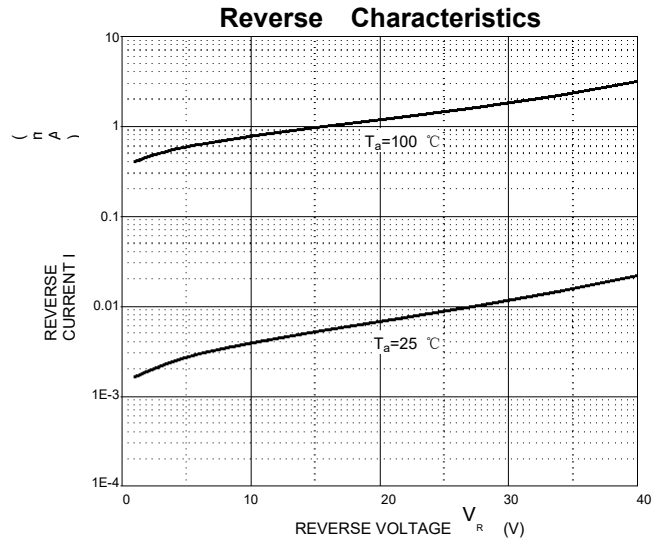
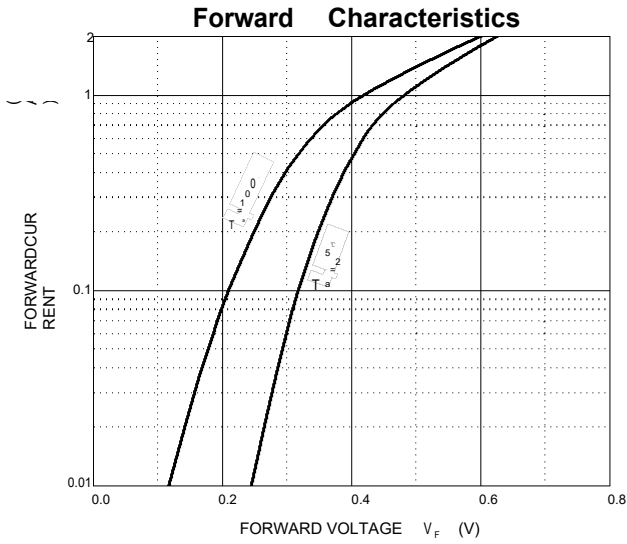
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Limits	Unit
DC reverse voltage	V_R	40	V
Mean rectifying current	I_o	1	A
Non-repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	I_{FSM}	15	A
Power Dissipation	P_D	350	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	285	$^\circ\text{C}/\text{W}$
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature	T_{stg}	-55~+150	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1\text{ A}$	V_F	0.51	V
Reverse Current at $V_R = 40\text{ V}$	I_R	30	μA

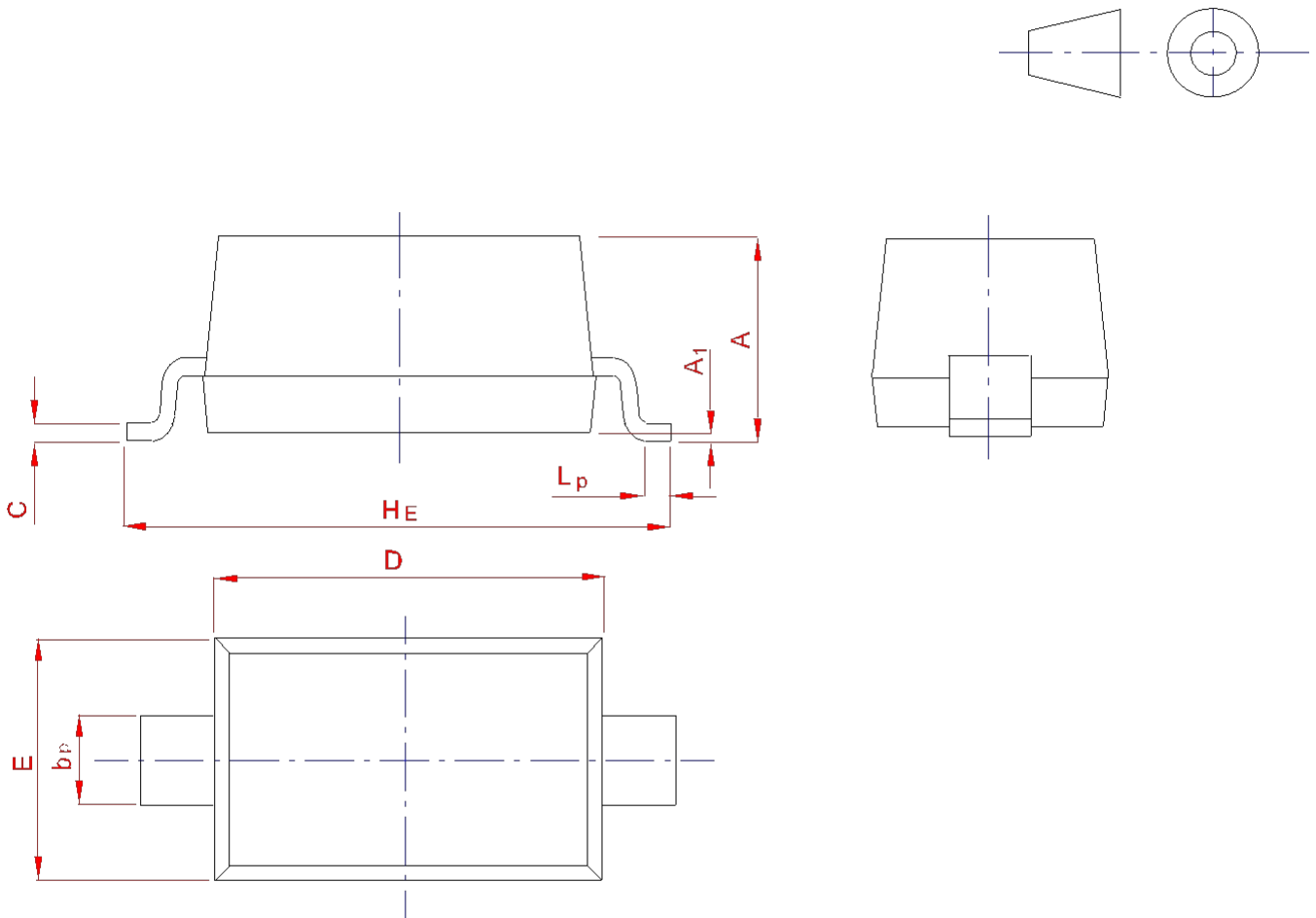
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-123



UNIT	A	bp	C	D	E	HE	A1	Lp
mm	1.20	0.60	0.135	2.75	1.65	3.85	0.10	0.50
	0.90	0.50	0.100	2.55	1.55	3.55	0.01	0.20